



LGE 320N10T

N-MOSFET TOLL 100V, 320A, 1.5mΩ



Features

- Uses advanced SGT technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)

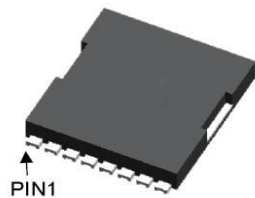
Application

- Motor control and drives
- Battery management
- DC/DC converter
- General purpose applications

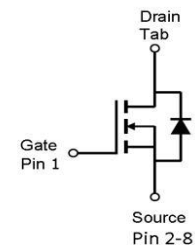
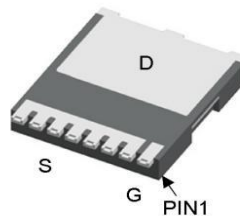
Product Summary

	TOLL
V_{DS}	100V
$R_{DS(on)}@V_{GS}=10V$	1.5mΩ
I_D	320A

TOLL Top View



TOLL Bottom View



Package Marking and Ordering Information

Type	Package	Marking	Reel Size	Tape Width	Packing	Qty
LGE 320N10T	TOLL	LGE 320N10T	330*28.5mm	24mm	Reel&Tape	2000

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	320 260 208	A
Pulsed drain current, $T_C = 25^\circ\text{C}$	$I_{D\text{ pulse}}$	1200	
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	E_{AS}	1936	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25^\circ\text{C}$	P_D	250	W
Operating junction and storage temperature	T_j, T_{stg}	-55~150	$^\circ\text{C}$



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Thermal Resistance

	Symbol	TYP	MAX	Unit
Thermal resistance, junction – case	R_{thJC}	0.35	0.5	°C/W
Thermal resistance, junction – ambient	R_{thJA}	30	40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	

Static Characteristic

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$ $T_j=25^\circ\text{C}$	2	3	4	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$ $T_j=25^\circ\text{C}$	-	-	1	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=30A$ $T_j=25^\circ\text{C}$	-	1.5	1.8	$m\Omega$
Transconductance	g_{fs}	$V_{DS}=5V, I_D=50A$	-	238	-	S

Dynamic Characteristic

Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=50V$ $f=1\text{MHz}$	-	10120	-	pF
Output Capacitance	C_{oss}		-	1360	-	
Reverse Transfer Capacitance	C_{rss}		-	50	-	
Gate Total Charge	Q_G	$V_{GS}=10V, V_{DS}=50V$ $I_D=50A$	-	175	-	nC
Gate-Source charge	Q_{gs}		-	50	-	
Gate-Drain charge	Q_{gd}		-	53	-	
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}, V_{GS}=10V$ $V_{DS}=50V, R_L=6\Omega$	-	85	-	ns
Rise time	t_r		-	138	-	
Turn-off delay time	$t_{d(off)}$		-	93	-	
Fall time	t_f		-	98	-	
Gate resistance	R_G	$V_{GS}=0V, V_{DS}=0V$ $f=1\text{MHz}$	-	1.7	-	Ω



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Body Diode Characteristic

Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=50A$	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F=30A,$ $dI/dt=500A/\mu s$	-	47	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=30A,$ $dI/dt=100A/\mu s$	-	388	-	nC

Typical Performance Characteristics

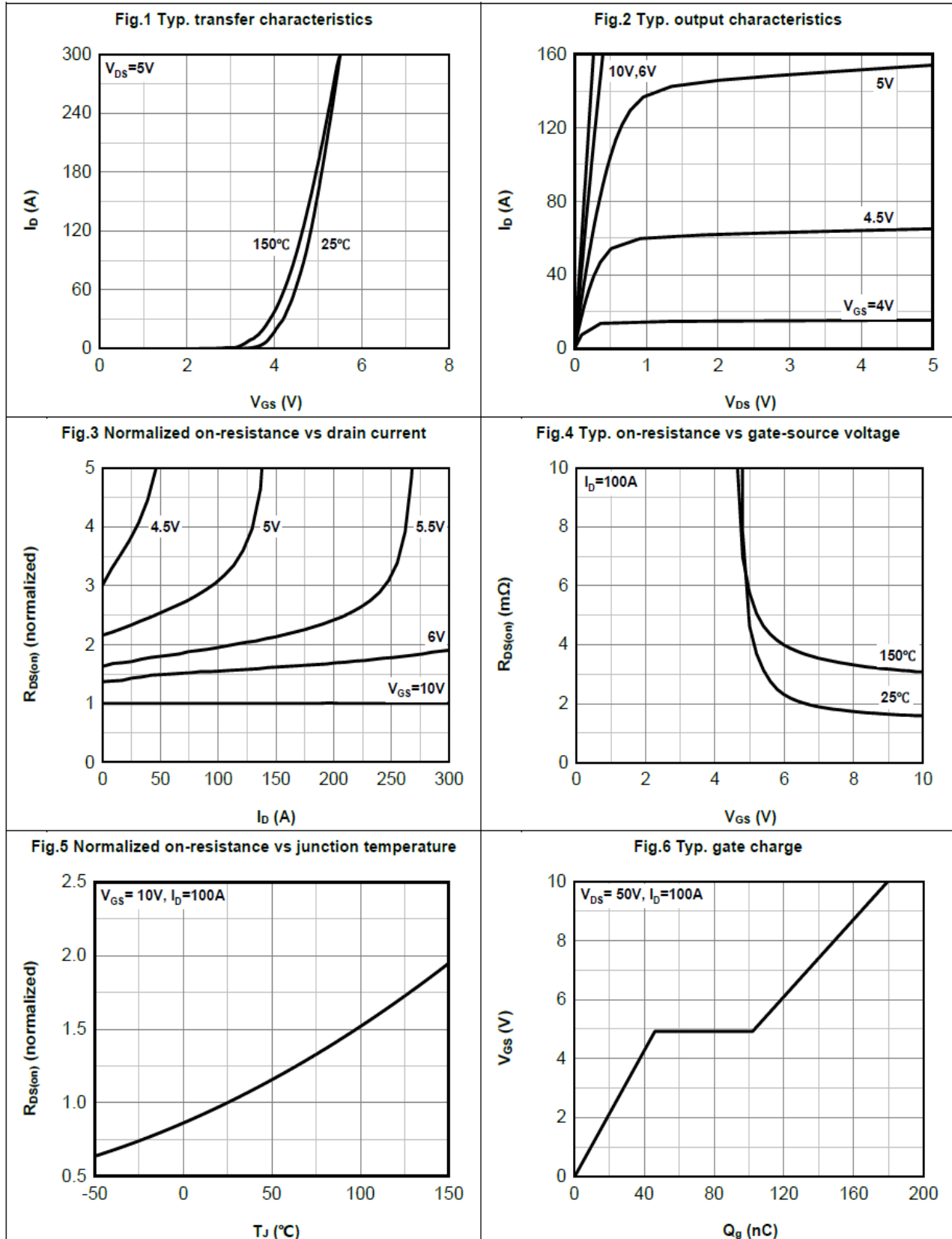


Fig.7 Typ. forward characteristics of body diode

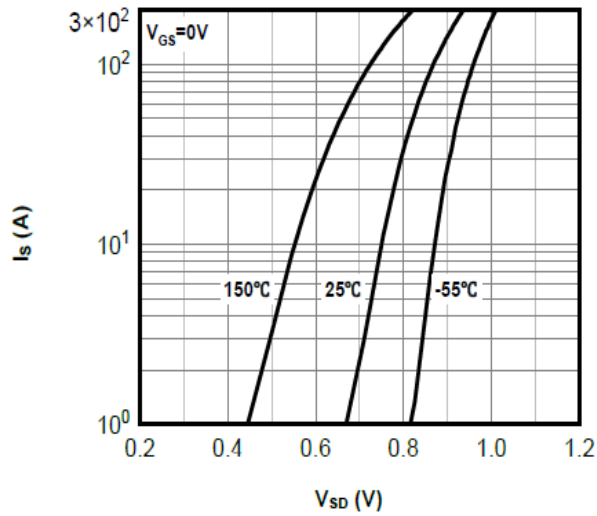


Fig.8 Safe operating area

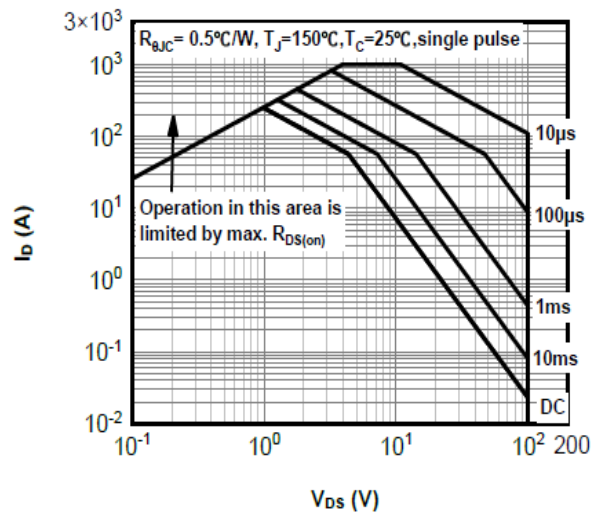


Fig.9 Typ. Capacitance

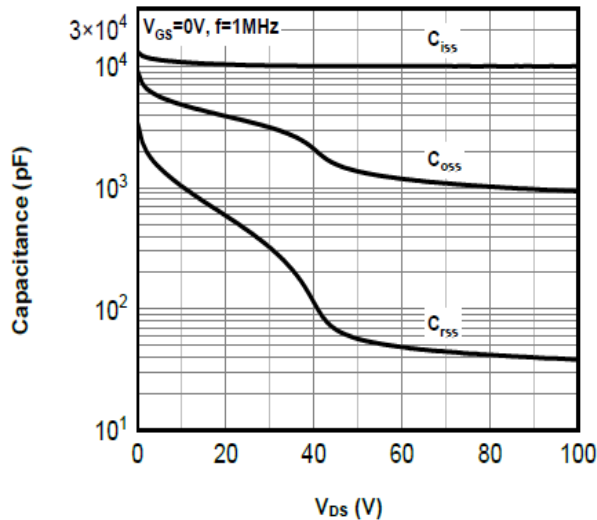


Fig.10 Single pulse maximum power dissipation

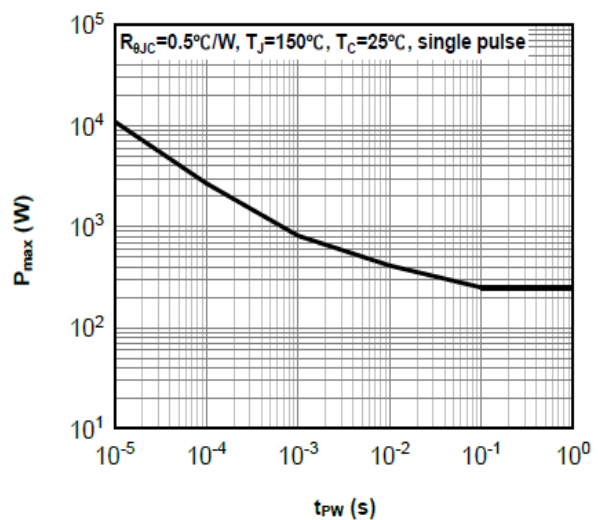


Fig.11 Max. power dissipation vs case temperature

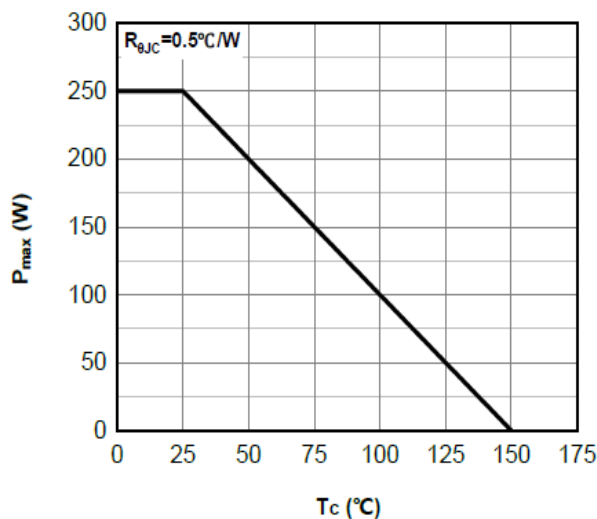


Fig.12 Max. continuous drain current vs case temperature

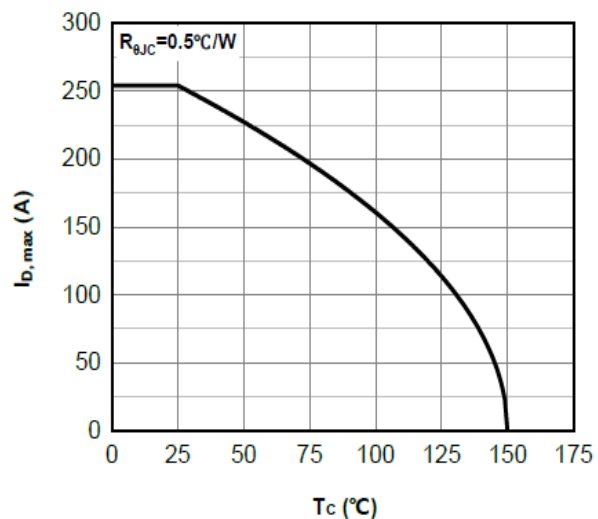


Fig.13 Normalized $V_{(BR)DSS}$ vs junction temperature

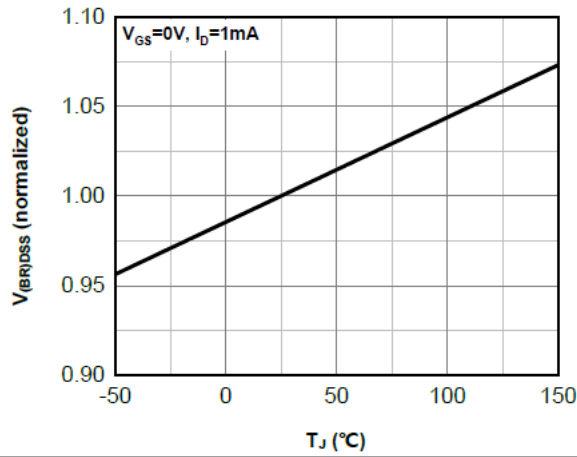


Fig.14 Normalized $V_{GS(th)}$ vs junction temperature

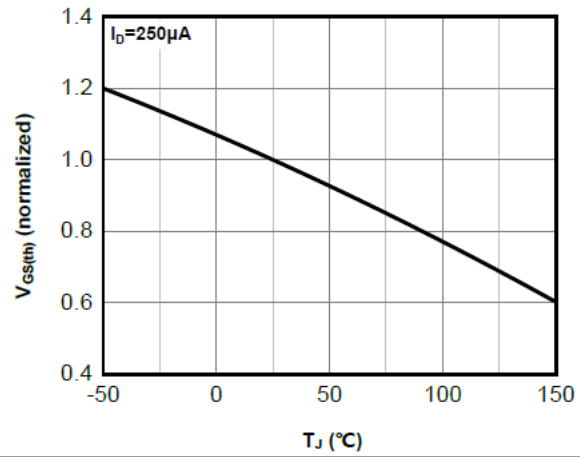
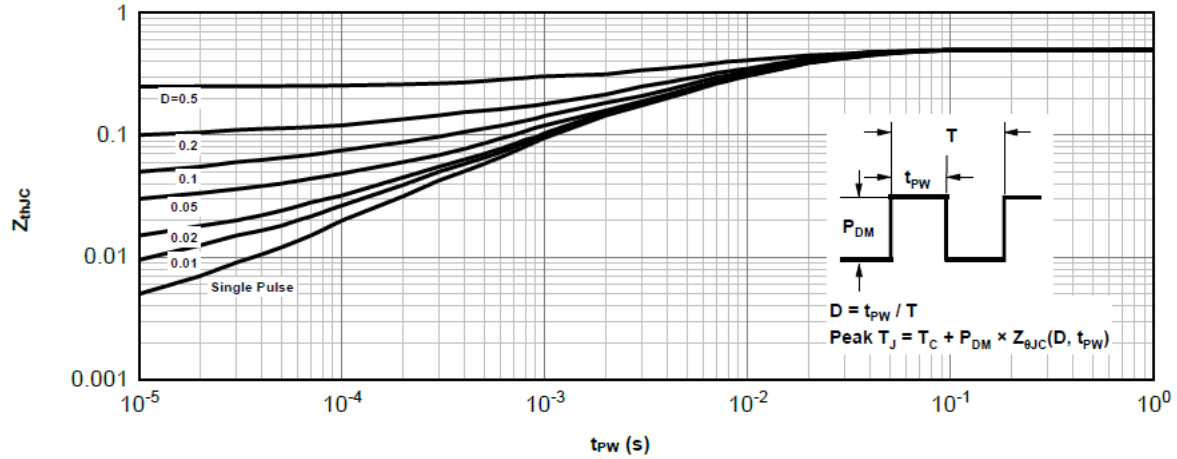
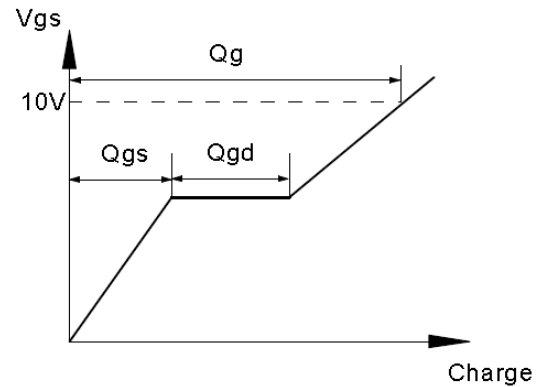
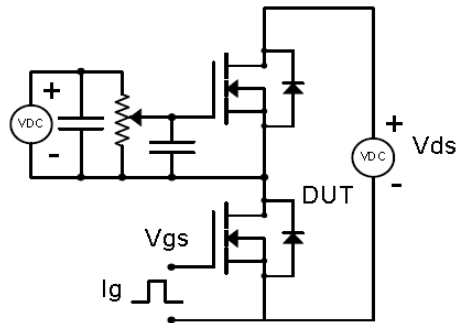


Fig.15 Transient thermal impedance from junction to case

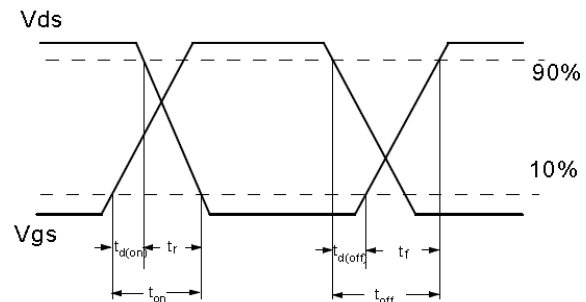
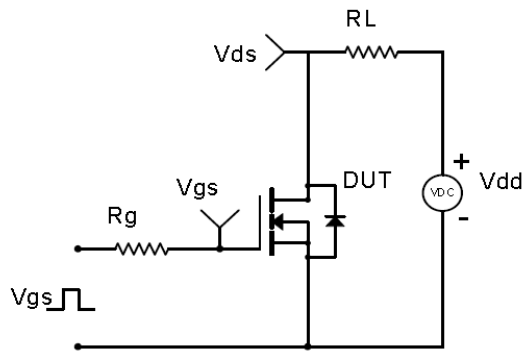


Test Circuit & Waveform

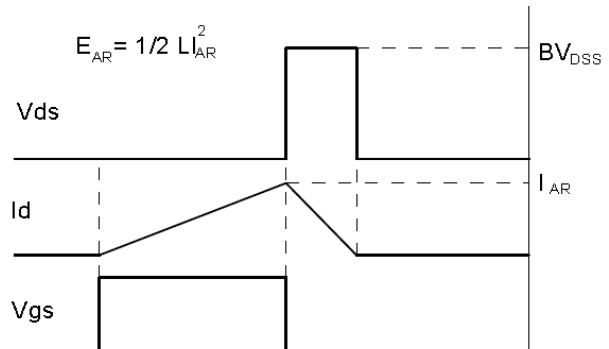
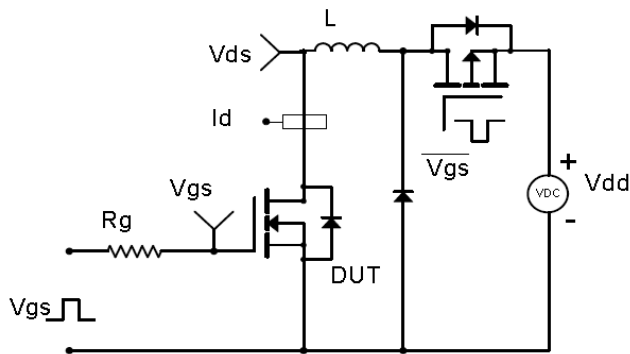
Gate Charge Test Circuit & Waveform



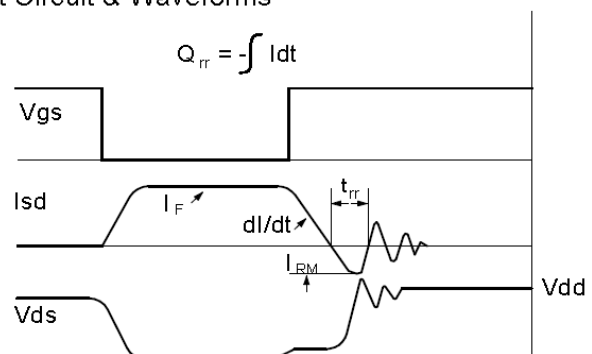
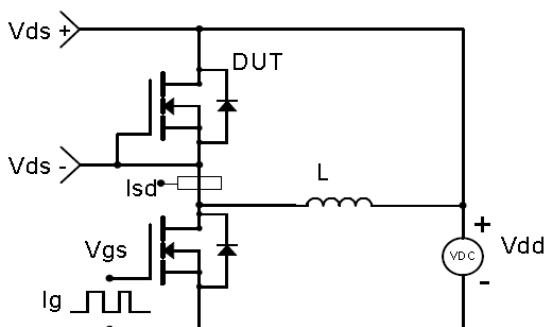
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



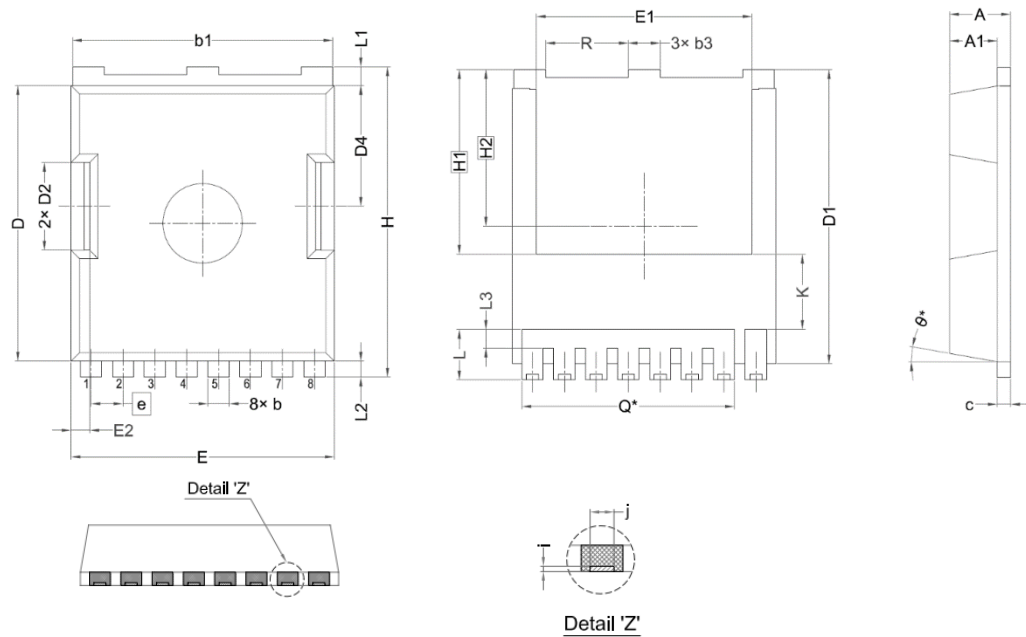


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Package Outline:TOLL



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	2,20	2,30	2,40
A1	1,70	1,80	1,90
b	0,70	0,80	0,90
b1	9,70	9,80	9,90
b3	1,10	1,20	1,30
c	0,40	0,50	0,60
D	10,28	10,38	10,48
D1	10,98	11,08	11,18
D2	3,20	3,30	3,40
D4	4,45	4,55	4,65
E	9,80	9,90	10,00
E1	8,00	8,10	8,20
E2	0,60	0,70	0,80
e	1,20 BSC		
H	11,58	11,68	11,78
H1	6,95 BSC		
H2	5,89 BSC		
I	0,10 REF.		
j	0,46 REF.		
K	2,80 REF.		
L	1,40	1,90	2,10
L1	0,60	0,70	0,80
L2	0,50	0,60	0,70
L3	0,30	0,70	0,80
N	8		
Q	8,00 REF.		
R	3,00	3,10	3,20
θ	10° REF.		